优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistor, R1 Only
- Surface Mount Package Suited for Automated Assembly

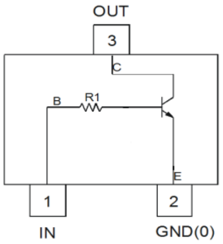
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, “Green” Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

Part Number	R1(NOM)
NK-DDTC113TUA	1kΩ
NK-DDTC123TUA	2.2kΩ
NK-DDTC143TUA	4.7kΩ
NK-DDTC114TUA	10kΩ
NK-DDTC124TUA	22kΩ
NK-DDTC144TUA	47kΩ
NK-DDTC115TUA	100kΩ
NK-DDTC125TUA	200kΩ

SOT323

Top View



Device Schematic

Absolute Maximum Ratings NPN Section (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C (Max)	100	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Note: 5. Mounted on FR4 PC Board with minimum recommended pad layout.

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 50μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	I_E = 50μA
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	V_{CB} = 50V
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	V_{EB} = 4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	I_C/I_B = 10mA/1mA NK-DDTC113TUA I_C/I_B = 5mA/0.5mA NK-DDTC123TUA I_C/I_B = 2.5mA/0.25mA NK-DDTC143TUA I_C/I_B = 1mA/0.1mA NK-DDTC114TUA I_C/I_B = 5mA/0.5mA NK-DDTC124TUA I_C/I_B = 2.5mA/0.25mA NK-DDTC144TUA I_C/I_B = 1mA/0.1mA NK-DDTC115TUA I_C/I_B = 0.5mA/0.05mA NK-DDTC125TUA
DC Current Transfer Ratio	h_{FE}	100	250	600	—	I_C = 1mA, V_{CE} = 5V
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Gain-Bandwidth Product (Note 6)	f_T	—	250	—	MHz	V_{CE} = 10V, I_E = -5mA, f = 100MHz

Note 6. Transistor only.

Typical Curves – NK-DDTC114TUA (@ T_A = +25°C, unless otherwise specified.)

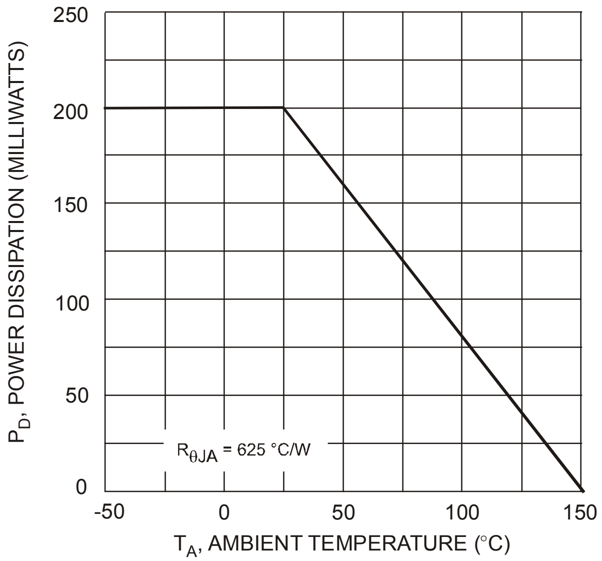


Fig. 1 Derating Curve

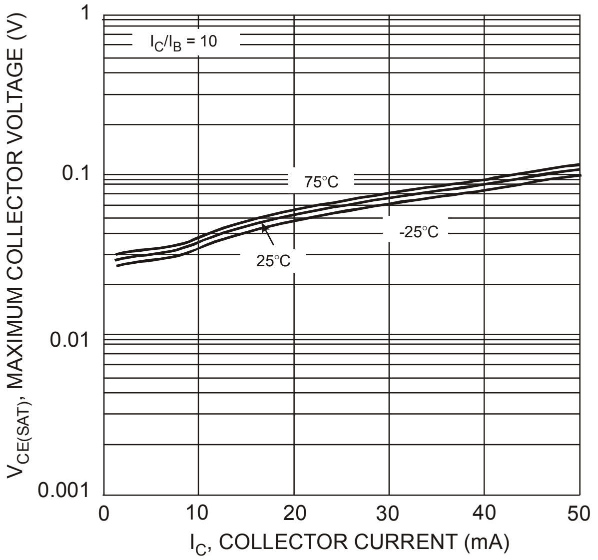


Fig. 2 $V_{CE(SAT)}$ vs. I_C

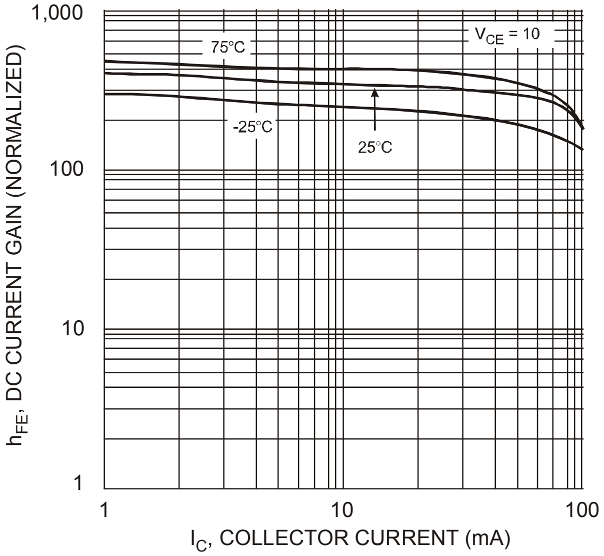


Fig. 3 DC Current Gain

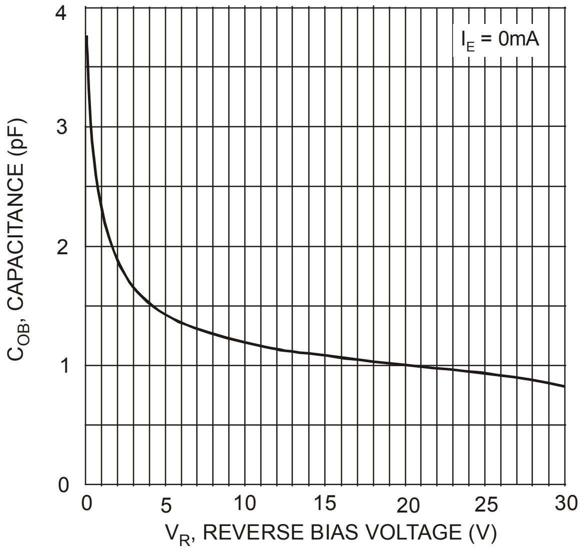


Fig. 4 Output Capacitance

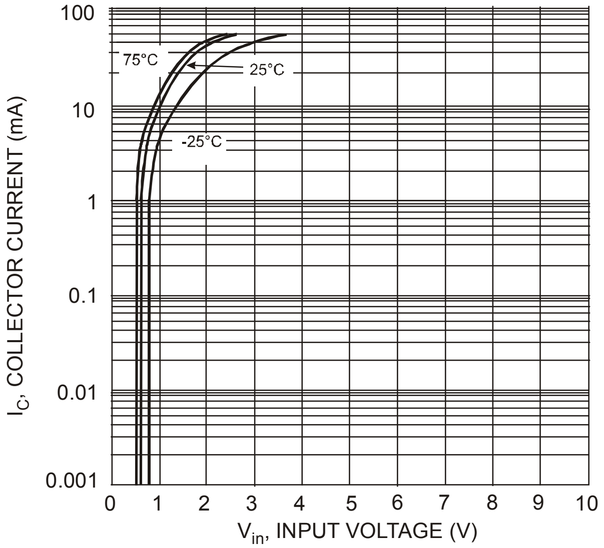


Fig. 5 Collector Current vs. Input Voltage

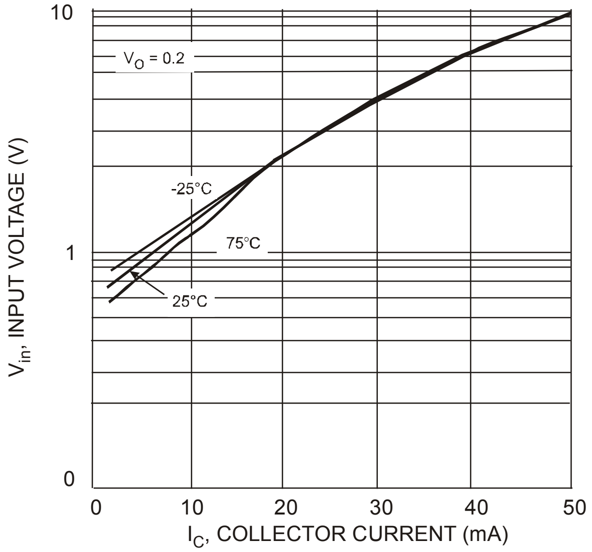


Fig. 6 Input Voltage vs. Collector Current

Package Outline Dimensions

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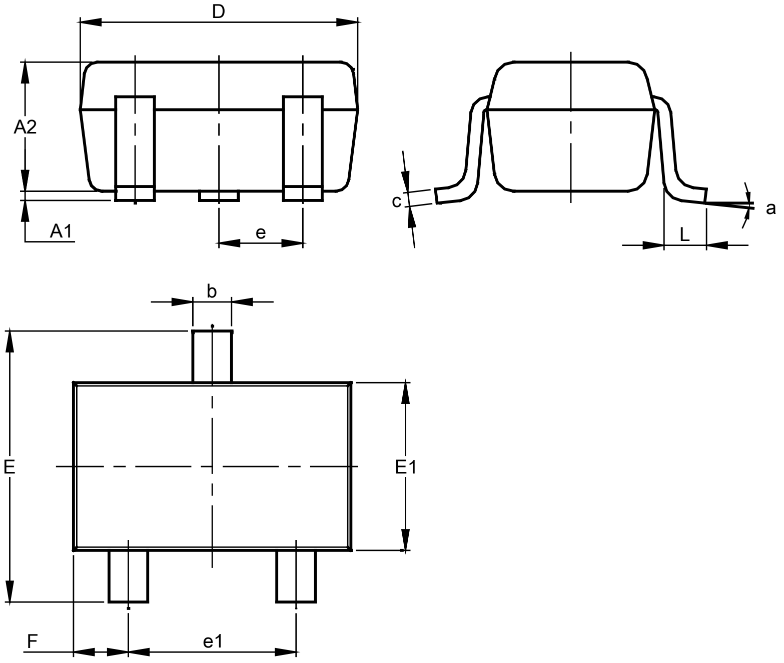

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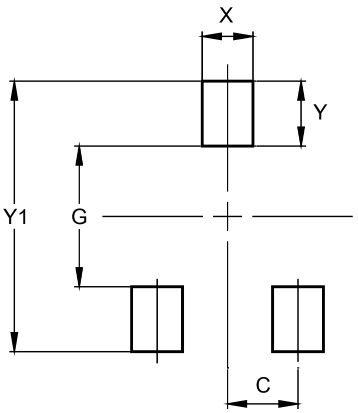
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500